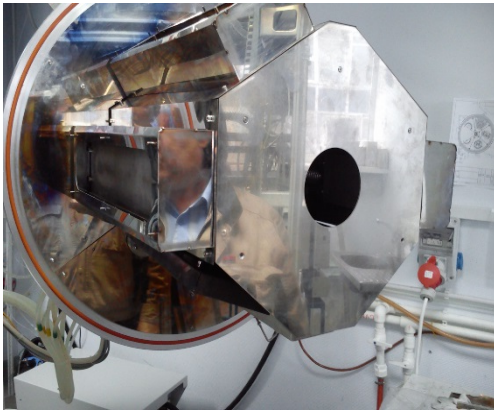
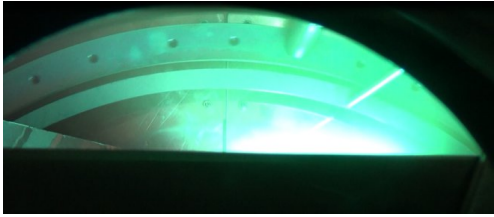


Magnetron M-250



Magnetron M-250

When using a pulsed medium-frequency power supply, it is possible to deposit semiconductors, as well as dielectrics in a reactive mode, from metal targets.

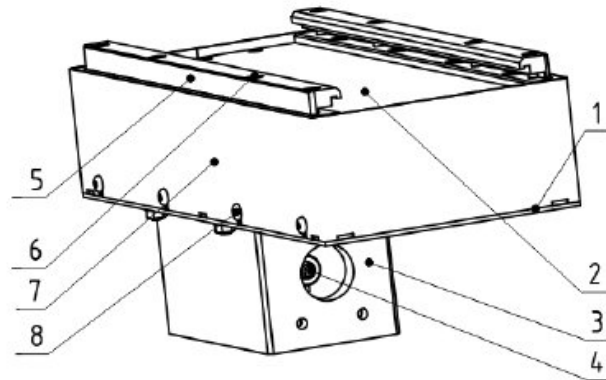
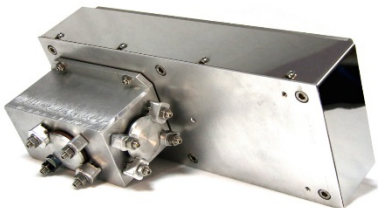
Extended magnetron M-250 is designed for applying thin films of various materials on a substrate in a vacuum. In the constant current mode, it is possible to deposit metals, alloys (including resistive ones) while maintaining the stoichiometric composition.

Parameter	Value
Maximum power	12 000 W
Maximum current	20 A
Maximum voltage	2000 V
Target size (length x width)	250 x 94
	<i>Height 6 mm (for magnetic, 10 for non-magnetic)</i>
Weight	8,8 kg (no more than)
Chamber working pressure range	0,10 – 10 Pa
Working gases	Ar, O ₂ , N ₂ , Xe, CH ₄ , C ₂ H ₂
Coolant consumption	2 l/min at 3 kW, 4 l/min at 7 kW, 5 l/min at 12 kW

The design allows for various combinations of magnetron placement in the chamber

Magnetron M-250

basic dimensions



1. plate with housing and magnetic system
2. refrigerated target holder
3. box
4. coolant vacuum connections and supply voltage
5. clamps
6. clamp screws
7. screen
8. shield fixing screws

